





6A TRIACs BTA06



TO-220A
Package
Plastic Insulated
RoHS compliant

DESCRIPTION

With high ability to withstand the shock loading of large current, BTA06 series triacs provide high dv/dt rate with strong resistance to electromagnetic interface. With high commutation performances, the products especially recommended for use on inductive load. From all three terminals to external heatsink, BTA06A provides a rated insulation voltage of 2500 VRMS, The package is RoHS compliant. (2011/65/EU)

MAIN FEATURES

Parameter	Symbol	Value	Unit
RMS on-state current	I _{T(RMS)}	6	Α
Non repetitive surge peak Off-state voltage/ Repetitive peak reverse voltage(Tj=25°C)	V_{DRM}/V_{RRM}	600/800	٧

ABSOLUTE MAXIMUM RATINGS

Parameter			Symbol	Value	Unit
Storage junction temperate	ture range		Tstg	-40-150	°C
Operating junction temper	rature range		Tj	-40-125	°C
Repetitive peak off-state	/oltage(Tj=25°0	C)	V_{DRM}	V _{DRM} 600/800	
Repetitive peak reverse v	oltage(Tj=25°C)	V_{RRM}	600/800	V
RMS on-state current	TO-220A (T	_C =100°C)	I _{T(RMS)}	6	Α
Non repetitive surge peak on-state current (full cycle, F=50Hz)			I _{TSM}	60	Α
I ² t value for fusing (tp=10ms)			l ² t	18	A^2s
Critical rate of rise of on-			dl/dt	50	A/µs
statecurrent(I _G =2×I _{GT}) IV				10	
Peak gate current			I _{GM}	2	Α
Average gate power dissipation			$P_{G(AV)}$	1	W
Peak gate power dissipation			P_GM	5	W

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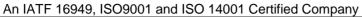


ELECTRICAL CHARACTERISTICS at $T_a = 25$ °C

Parameter	Symbol	Test Condition	Quadrant	Value		Unit
Farameter	Syllibol	rest condition	Quadrant	C	В	Ollit
Triggering gate current	I _{GT} (Max)		I - II - III	25	50	mA
Inggering gate current	igi (iviax)	VD=12V RL=33Ω	IV	50	75	III/A
Triggering gate voltage	V _{GT} (Max)		ALL	1.5		V
Non-triggering gate voltage	V _{GD} (Min)	V _D -V _{DRM} 1j-123 C, R. =3 3KO	ALL	0.2		V
Latching current	I _∟ (Max)	l _G =1.2l _{GT}	I -III-IV	50	70	mA
Laterling current	IL (IVIAX)	1G-1.21G	П	60	80	ША
Holding current	I _H (Max)	I _T =200mA	ALL	40	60	mA
Critical rate of rise of off-state voltage	dV/dt (Min)	V _D =2/3V _{DRM} Gate Open T _j =125°C		200	500	V/µs
STATIC CHARACTERIS	TICS				<u>l</u>	
Parameter	Symbol	Test Condition Temp.		Value (Max)		Unit
Peak on-state voltage drop	V_{TM}	I _{TM} =8.5A t _p =380μs	T _j =25°C	1.5		V
Max. Forward Current	I _{DRM}	$V_D = V_{DRM} V_R = V_{RRM}$	T _j =25°C	5		μΑ
Max. Reverse Current	I _{RRM}	VD=VDRM VR=VRRM	T _j =125°C	1		mA
THERMAL RESISTANCES						
Parameter	Symbol	Test Condition	Value (Max)			Unit
Junction to case thermal resistance	$R_{\text{th(j-c)}}$	Junction to case(AC) 2.9			°C/W	



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Typical Characteristic curves

FIG.1: Maximum power dissipation versus RMS on-state current

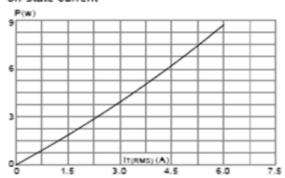


FIG.3: Surge peak on-state current versus number of cycles

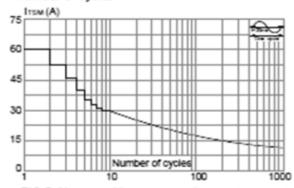


FIG.5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width tp<20ms, and corresponging value of I^2t ($I - II - III : dI/dt < 50A/\mu s$; $IV : dI/dt < 10A/\mu s$)

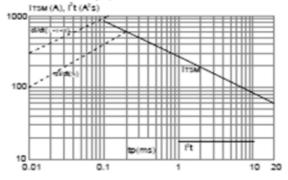


FIG.2: RMS on-state current versus case temperature

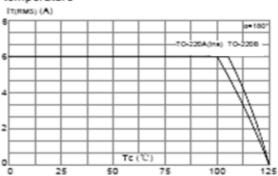


FIG.4: On-state characteristics (maximum values)

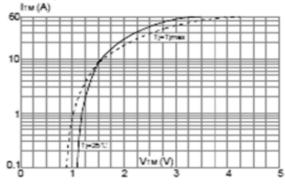
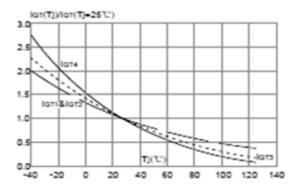


FIG.6: Relative variations of gate trigger current versus junction temperature



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Typical Characteristic curves (continoue....)

FIG.7: Relative variations of holding current versus junction temperature

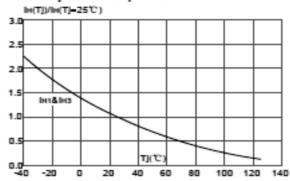
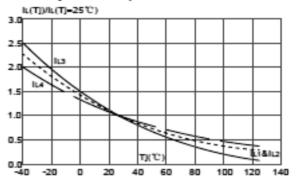


FIG.8: Relative variations of latching current versus junction temperature



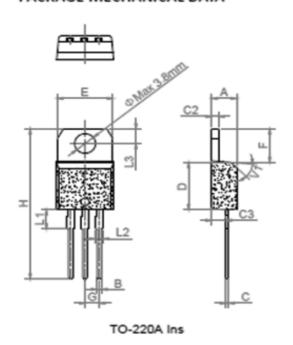






Package Details

PACKAGE MECHANICAL DATA



	Dimensions					
Ref.	Millimeters		Inches			
	Min.	Тур.	Max.	Min.	Тур.	Max.
Α	4.40		4.60	0.173		0.181
В	0.61		0.88	0.024		0.035
С	0.46		0.70	0.018		0.028
C2	1.21		1.32	0.048		0.052
ಜ	2.40		2.72	0.094		0.107
D	8.60		9.70	0.339		0.382
Ε	9.80		10.4	0.386		0.409
F	6.55		6.95	0.258		0.274
G		2.54			0.1	
Н	28.0		29.8	1.102		1.173
L1		3.75			0.148	
L2	1.14		1.70	0.045		0.067
L3	2.65		2.95	0.104		0.116
V1		45°			45°	

Note: For AECQ compliant products, please suffix -AH in the part number while ordering

PACKAGE	WEIGHT (Per PCS)	OUTLINE	TUBE (PCS)	INNER BOX (PCS)	PER CART ON
TO-220A	2.308 gm	TUBE	50	1,000	8,000





Recommended Product Storage Environment for Diode and Transistors

This storage environment assumes that the Diodes and transistors are packed properly inside the original packing supplied by CDIL.

- Temperature 5 °C to 30 °C
- Humidity between 40 to 70 %RH
- Air should be clean.
- · Avoid harmful gas or dust.
- · Avoid outdoor exposure or storage in areas subject to rain or water spraying .
- Avoid storage in areas subject to corrosive gas or dust. Product shall not be stored in areas exposed to direct sunlight.
- · Avoid rapid change of temperature.
- · Avoid condensation.
- Mechanical stress such as vibration and impact shall be avoided.
- The product shall not be placed directly on the floor.
- The product shall be stored on a plane area. They should not be turned upside down. They should not be placed against the wall.

Shelf Life of CDIL Products

The shelf life of products is the period from product manufacture to shipment to customers. The product can be unconditionally shipped within this period. The period is defined as 2 years.

If products are stored longer than the shelf life of 2 years, the products shall be subjected to quality check as per CDIL quality procedure.

The products are further warranted for another one year after the date of shipment subject to the above conditions in CDIL original packing.

Floor Life of CDIL Products and MSL Level

When the products are opened from the original packing, the floor life will start. For this the following JEDEC table may be referred:

JEDEC MSL Level				
Level	Time	Condition		
1	Unlimited	≤30 °C / 85% RH		
2	1 Year	≤30 °C / 60% RH		
2a	4 Weeks	≤30 °C / 60% RH		
3	168 Hours	≤30 °C / 60% RH		
4	72 Hours	≤30 °C / 60% RH		
5	48 Hours	≤30 °C / 60% RH		
5a	24 Hours	≤30 °C / 60% RH		
6	Time on Label(TOL)	<30 °C / 60% RH		

Figure 1 Floor Life according to JEDEC MSL Level







Customer Notes

Component Disposal Instructions

- 1. CDIL Semiconductor Devices are RoHS compliant, customers are requested to please dispose as per prevailing Environmental Legislation of their Country.
- 2. In Europe, please dispose as per EU Directive 2002/96/EC on Waste Electrical and Electronic Equipment (WEEE).

Disclaimer

The product information and the selection guides facilitate selection of the CDIL's Semiconductor Device(s) best suited for application in your product(s) as per your requirement. It is recommended that you completely review our Data Sheet(s) so as to confirm that the Device(s) meet functionality parameters for your application. The information furnished in the Data Sheet and on the CDIL Web Site/CD are believed to be accurate and reliable. CDIL however, does not assume responsibility for inaccuracies or incomplete information. Furthermore, CDIL does not assume liability whatsoever, arising out of the application or use of any CDIL product; neither does it convey any license under its patent rights nor rights of others. These products are not designed for use in life saving/support appliances or systems. CDIL customers selling these products (either as individual Semiconductor Devices or incorporated in their end products), in any life saving/support appliances or systems or applications do so at their own risk and CDIL will not be responsible for any damages resulting from such sale(s).

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